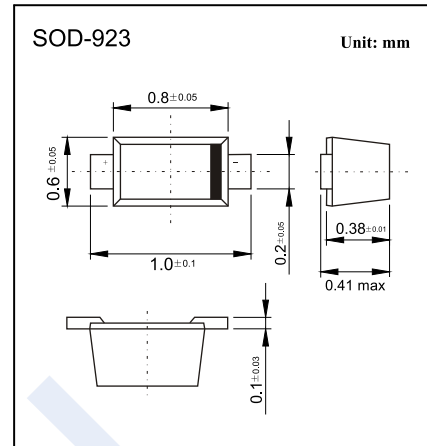


ESD Protection Diodes

ESD9B5V

■ Features

- Low Leakage
- Fast Response Time < 1 ns
- Protects One Power or I/O Port
- ESD Rating of Class 3 (>16KV) per Human Body Model



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
IEC 61000-4-2 (ESD) Contact		±8	KV
IEC 61000-4-2 (EFT)		40	A
Power Dissipation (Note 1)	P _D	150	mW
Thermal Resistance Junction to Ambient	R _{θJA}	400	°C/W
Lead Solder Temperature - Maximum (10 Second Duration)	T _L	260	°C
Junction Temperature	T _J	150	
Storage Temperature range	T _{stg}	-55 to 150	

Note.1:FR-5 = 1.0*0.75*0.62 in.

■ Electrical Characteristics Ta = 25°C

Device	Device Marking	V _{RWM} (V)	I _R (uA) @ V _{RWM}	V _{BR} (V) @ I _T (Note 1)		I _T (mA)	C (pF)
		Max	Max	Min	Max		
ESD9B5V		5.0	1.0	5.8	7.8	1.0	15

Note.1. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C

ESD Protection Diodes

ESD9B5V

■ Typical Characteristics

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
I_T	Test Current
V_{BR}	Breakdown Voltage @ I_T

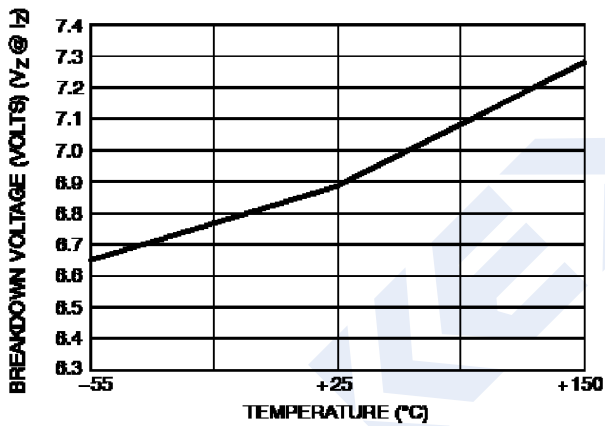
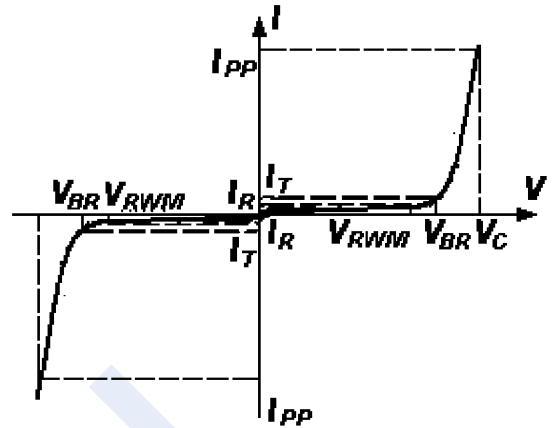


Figure 1. Typical Breakdown Voltage versus Temperature

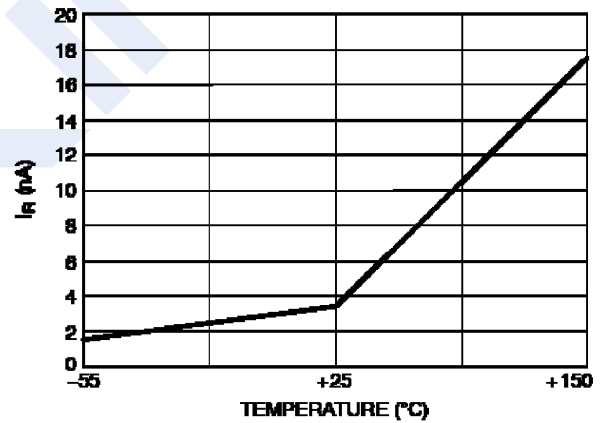


Fig 2. Typical Leakage Current versus Temperature